

N-channel 100V 13.9mΩ standard level MOSFET in I2PAK. Rev. 3 — 29 September 2011 Product data s

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	U
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	68	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 11</u>		-	-	25	mΩ
	resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	[2]	-	11	13.9	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 50 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 13}$		-	17	-	nC

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Table 1.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{G(tot)}	total gate charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ V_{DS} = 50 \text{ V}; \text{ see } \underline{\text{Figure } 13}; \\ \text{see } \underline{\text{Figure } 14} \end{array}$	-	59	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	127	mJ

[1] Continuous current is limited by package.

[2] Measured 3 mm from package.

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT226 (I2PAK)

 $\begin{bmatrix} 2 & 2 \\ 1 & 2 & 3 \end{bmatrix}$

3. Ordering information

Table 3. Ordering in	nformation		
Type number	Package		
	Name	Description	Version
PSMN013-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

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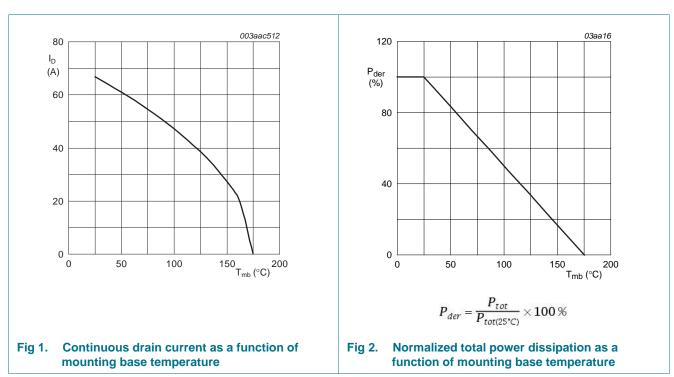
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	47	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	68	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	272	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	170	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					
ls	source current	T _{mb} = 25 °C	[1]	-	68	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	272	А
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 68 A; $V_{sup} \le 100$ V; unclamped; R_{GS} = 50 Ω		-	127	mJ

[1] Continuous current is limited by package.



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5. Thermal characteristics

Parameter	Conditions	Min	Тур	Max	Unit
thermal resistance from junction to mounting base	see Figure 3	-	0.5	0.9	K/W
thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W
	thermal resistance from junction to mounting base	thermal resistance from junction to mounting base see Figure 3	thermal resistance from junction to mounting base see Figure 3 -	thermal resistance from junction to mounting base see <u>Figure 3</u> - 0.5	thermal resistance from junction to mounting base see Figure 3 - 0.5 0.9

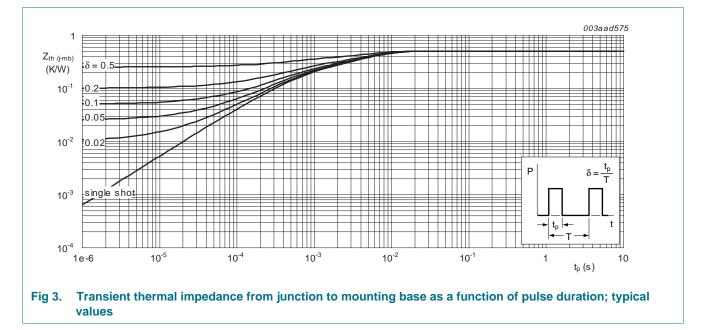


Table 5. Thermal characteristics

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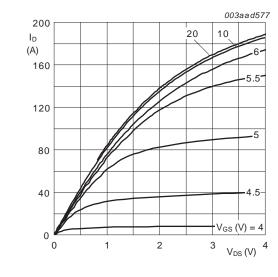
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)} gate-so	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 9	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 9	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10	-	-	4.8	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	100	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.06	2	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 11</u>	-	30	38.9	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 11</u>	-	-	25	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see Figure 12; see Figure 11	[1] -	11	13.9	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic	characteristics					
Q _{G(tot)} total gate charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14	-	59	-	nC	
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	47.6	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14	-	13.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	9.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4.6	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 13	-	17	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14;</u> see <u>Figure 13</u>	-	4.4	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3195	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{\text{Figure } 15}$	-	221	-	pF
C _{rss}	reverse transfer capacitance		-	136	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	20.7	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	25	-	ns
t _{d(off)}	turn-off delay time		-	52.5	-	ns
t _f	fall time		-	24	-	ns

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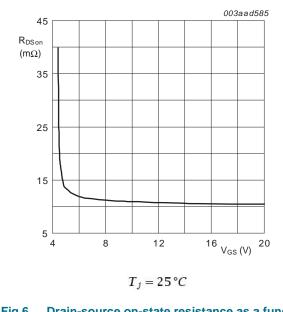
Table 6.	Characteristics continued							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Source-d	Source-drain diode							
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 16</u>	-	0.8	1.2	V		
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = 100 A/µs;	-	52	-	ns		
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 50 V$	-	109	-	nC		

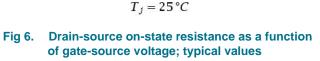
[1] Measured 3 mm from package.

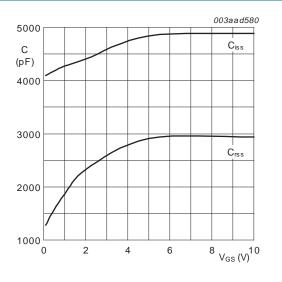


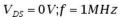




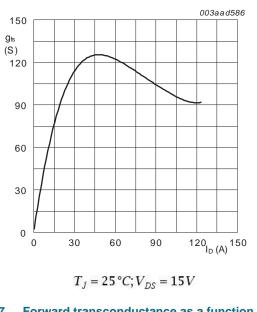














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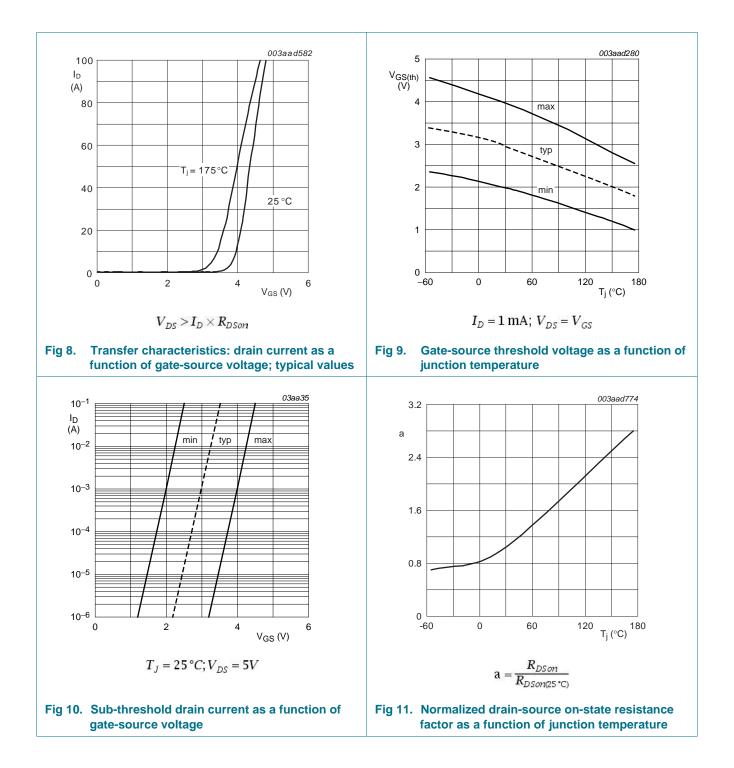
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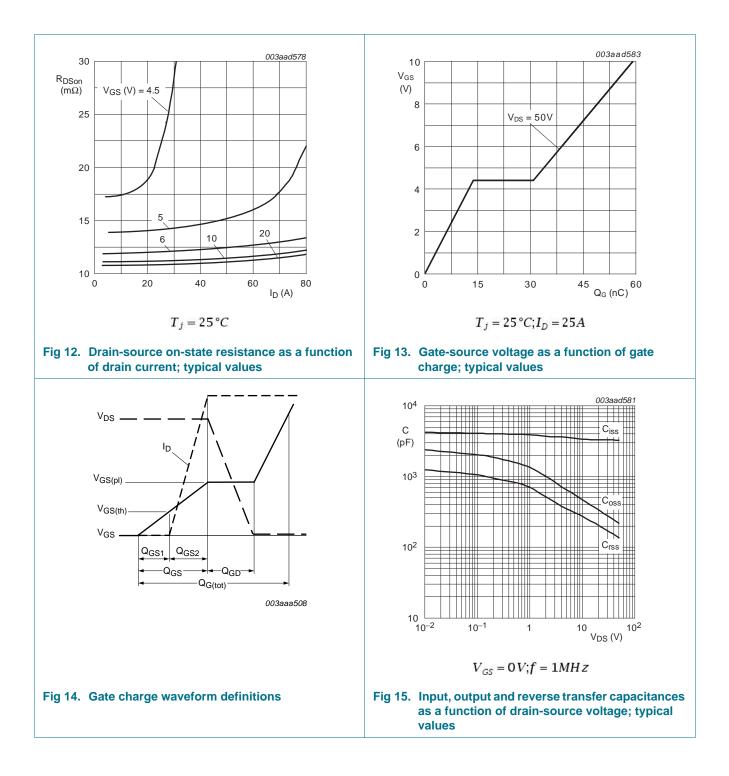
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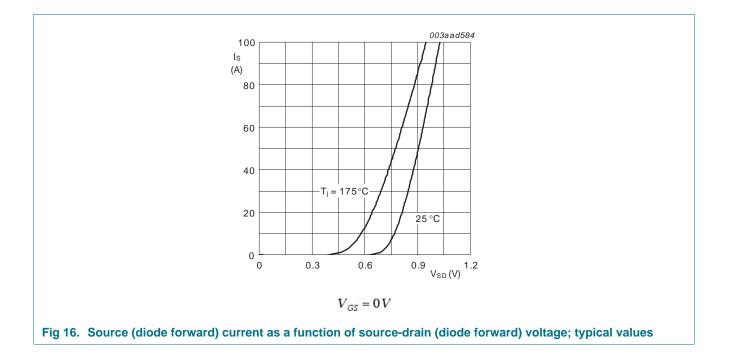
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7. Package outline

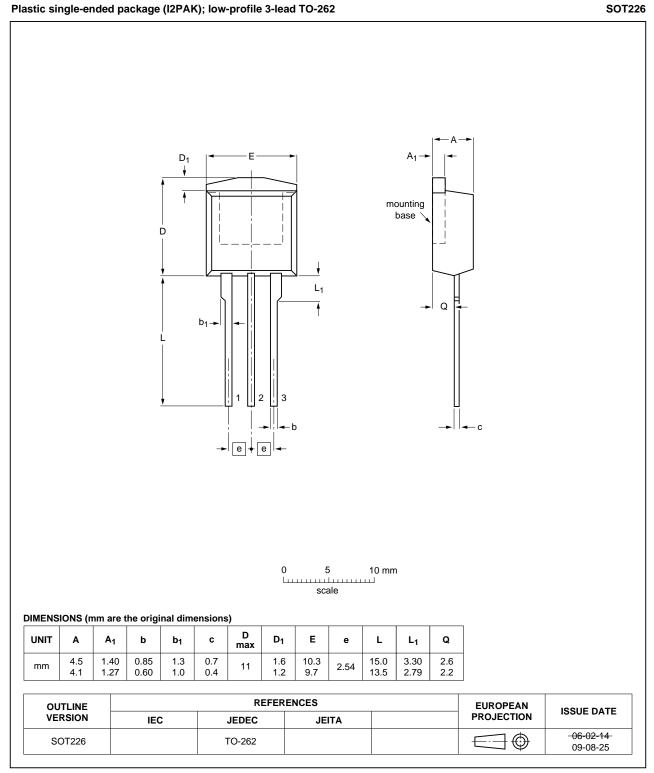


Fig 17. Package outline SOT226 (I2PAK)

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-100ES v.3	20110929	Product data sheet	-	PSMN013-100ES v.2
Modifications:	 Status change 	d from objective to product.		
	 Various change 	jes to content.		
PSMN013-100ES v.2	20100219	Objective data sheet	-	PSMN013-100ES v.1

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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